

ABSTRACT OF THE DISCLOSURE

Disclosed is a contact hole forming method capable of reducing parasitic capacitance between a conductive layer patterns, preventing bad contacts caused by mask misalignment and effectively filling an interlayer insulating layer between the conductive layer patterns. The method including forming many conductive layer patterns on a substrate, forming an interlayer insulating layer on a resulting structure where the conductive layer patterns are completed, exposing a conductive layer pattern which at least one sidewall of a contact region between conductive layer patterns is neighboring the contact region, and forming an insulating spacer on the sidewall of the exposed conductive layer pattern.